

ABSTRACT OF THE DISCLOSURE

A thin film transistor has a structure capable of decreasing deterioration in V_{gs} - I_{ds} characteristics. The thin film transistor has a source region composed of an N-type impurity-diffused region, a drain region, and a gate electrode, and a channel region formed directly below the gate electrode. To the source region and the drain region are connected a source electrode and a drain electrode, respectively, through a plurality of contact holes. In the channel region are formed a plurality of P-type impurity-diffused regions at constant intervals.